

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	6.5184	N/A	2.8857
RT2	16.2404	N/A	10.0216
RT3	19.9854	N/A	7.1811
RT4	42.2558	N/A	4.9116
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	836.8388 u	N/A	287.4216 u
CT2	21.3638 m	N/A	12.0686 m
CT3	261.7478 m	N/A	178.4418 m
CT4	1.9472	N/A	2.9403 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	7.9911	N/A	3.3048
RF2	18.0935	N/A	8.5179
RF3	22.5713	N/A	8.9650
RF4	36.3441	N/A	4.2123
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	944.8440 u	N/A	221.9511 u
CF2	21.6792 m	N/A	2.2687 m
CF3	232.9034 m	N/A	20.2984 m
CF4	1.9964	N/A	340.2701 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

